Conversion to Copper (Cu) Wire – SQ3427EV

For further information, please contact your regional Vishay office.

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Description of Change: The affected part number listed in this notification will be converted to a Copper wire material set. The new ordering code is SQ3427CEV-T1_GE3, which has the exact same product performance and fit as SQ3427EV. There will be no change to the wafer fab or assembly location (Note: parts with _BE3 suffix will be consolidated to a single assembly location at Simconix). There will be no changes to the parameters on the datasheet (reference: SQ3427CEV Doc # 62369 Rev.B).

Reason for Change: Standardization of materials

Expected Influence on Quality/Reliability/Performance: None

Part Numbers/Series/Families Affected: SQ3427EV-T1_GE3, SQ3427EV-T1_BE3,

Vishay Brand(S): Vishay Siliconix

Time Schedule:

Last Time Buy Date: Mon Jun 3, 2024

Last Time Ship Date: Tue Dec 3, 2024

Sample Availability: Qualified samples of replacement product are available on request

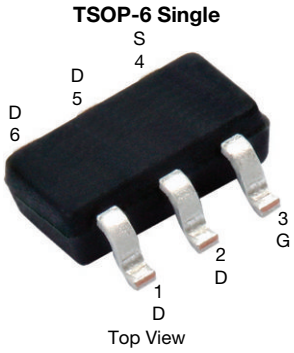
Product Identification: SQ3427CEV-T1_GE3

Qualification Data: AEC Q101 qualification data of replacement product is available. Qualification PPAP is available now.

This PTN is considered approved, without further notification, unless we receive specific customer concerns before Mon Jun 3, 2024 or as specified by contract.

Issued By: Lance Gurrola, automostechsupport@vishay.com

Automotive P-Channel 60 V (D-S) 175 °C MOSFET



FEATURES

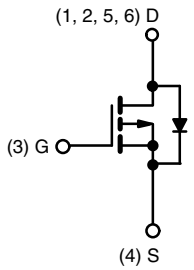
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

Pb-free

RoHS COMPLIANT

HALOGEN FREE



P-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	-60
$R_{DS(on)}$ (Ω) at V_{GS} = -10 V	0.095
$R_{DS(on)}$ (Ω) at V_{GS} = -4.5 V	0.135
I_D (A)	-5.3
Configuration	Single

Marking Code: 9Q

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3427CEV (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C	I_D	-5.3	A
	T_C = 125 °C		-3	
Continuous Source Current (Diode Conduction)		I_S	-6.3	
Pulsed Drain Current [a]		I_{DM}	-21	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	-21	
Single Pulse Avalanche Energy		E_{AS}	22	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	5	W
	T_C = 125 °C		1.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount [b]	R_{thJA}	110	°C/W
Junction-to-Foot (Drain)		R_{thJF}	30	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

b. When mounted on 1" square PCB (FR4 material).

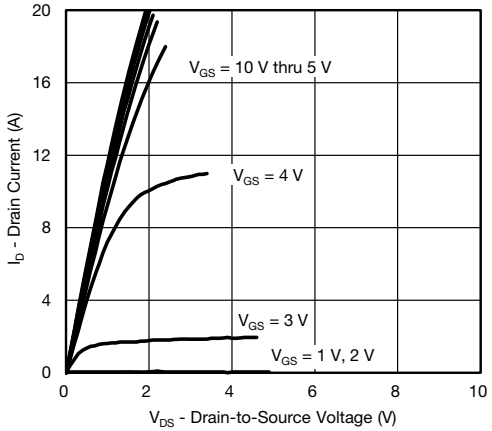
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = -250 µA		-60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA		-1.5	-2	-2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-		± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = -60 V	-	-	-1	µA
		V_{GS} = 0 V	V_{DS} = -60 V, T_J = 125 °C	-	-	-50	
		V_{GS} = 0 V	V_{DS} = -60 V, T_J = 175 °C	-	-	-150	
On-State Drain Current [a]	$I_{D(on)}$	V_{GS} = -10 V	V_{DS} ≤ -5 V	-10	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V	I_D = -4.5 A	-	0.079	0.095	Ω
		V_{GS} = -10 V	I_D = -4.5 A, T_J = 125 °C	-	-	0.148	
		V_{GS} = -10 V	I_D = -4.5 A, T_J = 175 °C	-	-	0.178	
		V_{GS} = -4.5 V	I_D = -3.5 A	-	0.112	0.135	
Forward Transconductance[a]	g_{fs}	V_{DS} = -15 V, I_D = -4 A		-	9	-	S
Dynamic [b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = -30 V, f = 1 MHz	-	726	1000	pF
Output Capacitance	C_{oss}			-	91	120	
Reverse Transfer Capacitance	C_{rss}			-	56	80	
Total Gate Charge [c]	Q_g	V_{GS} = -10 V	V_{DS} = -30 V, I_D = -5 A	-	16.9	22	nC
Gate-Source Charge [c]	Q_{gs}			-	2.9	-	
Gate-Drain Charge [c]	Q_{gd}			-	4.1	-	
Gate Resistance	R_g	f = 1 MHz		2.5	5	7.5	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = -30 V, R_L = 6 Ω I_D ≅ -5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	8	12	ns
Rise Time [c]	t_r			-	24	35	
Turn-Off Delay Time [c]	$t_{d(off)}$			-	25	38	
Fall Time [c]	t_f			-	33	50	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed Current [a]	I_{SM}			-	-	-21	A
Forward Voltage	V_{SD}	I_F = -1.6 A, V_{GS} = 0 V		-	-0.8	-1.2	V
Body diode reverse recovery time	t_{rr}	I_F = -1.7 A, di/dt = 100 A/µs		-	23	46	ns
Body diode reverse recovery charge	Q_{rr}			-	27	54	nC
Reverse recovery fall time	t_a			-	20	-	
Reverse recovery rise time	t_b			-	3	-	ns
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-2.86	-	A

Notes

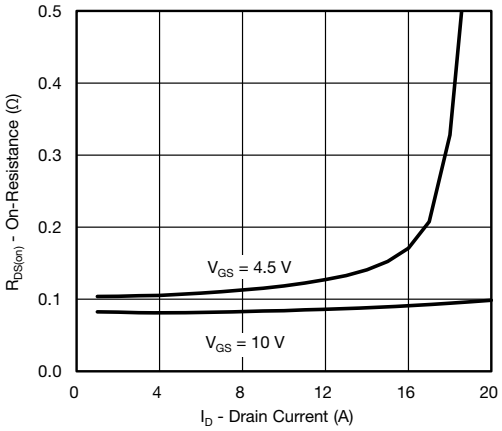
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

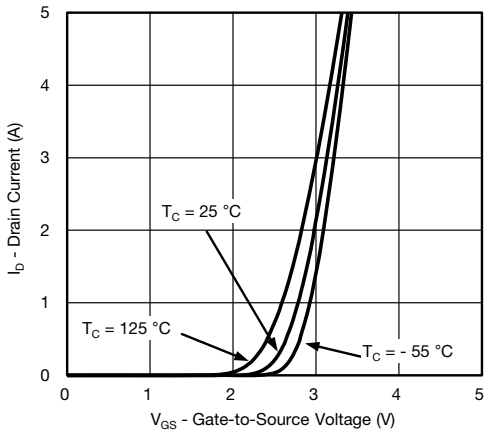
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



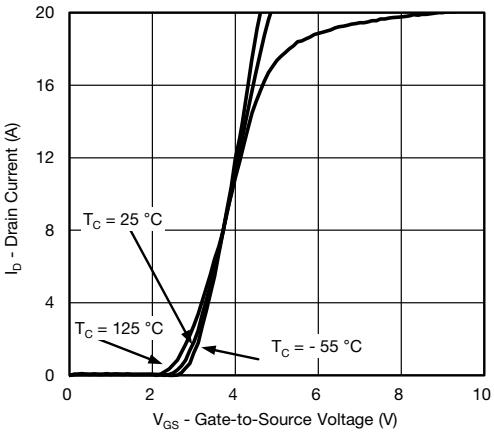
Output Characteristics



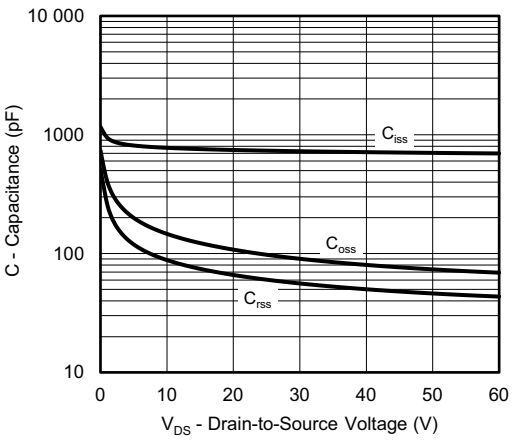
On-Resistance vs. Drain Current and Gate Voltage



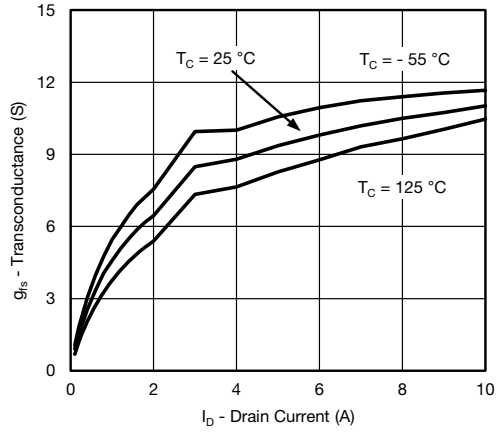
Transfer Characteristics



Transfer Characteristics

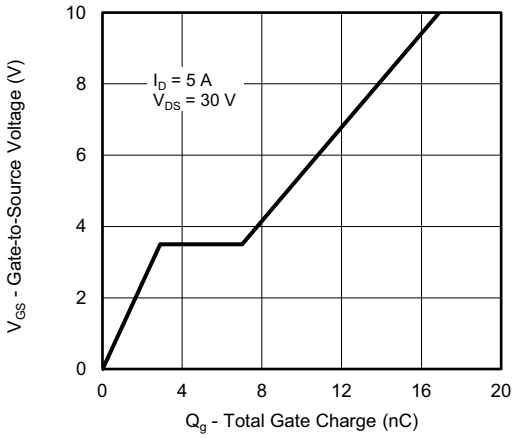


Capacitance

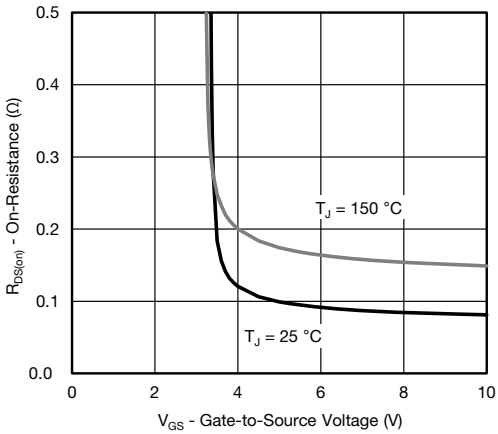


Transconductance

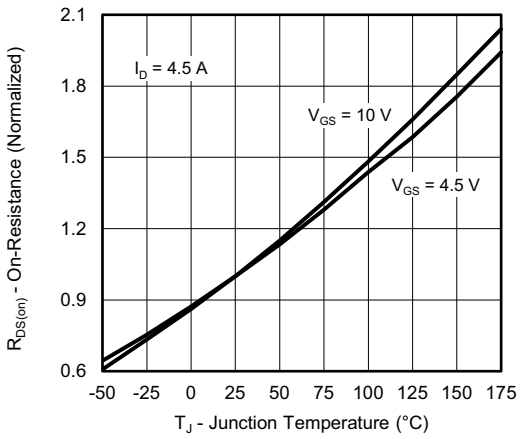
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



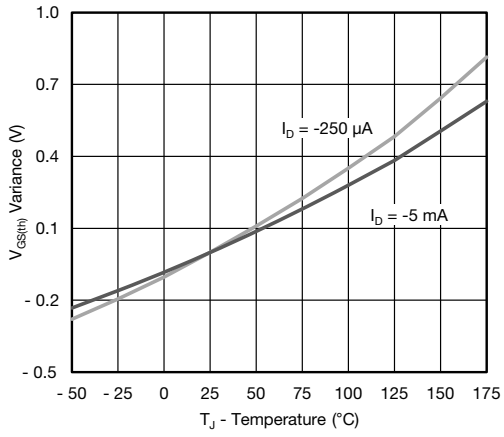
Gate Charge



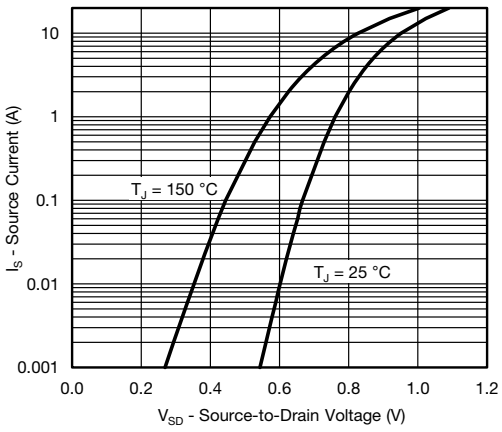
On-Resistance vs. Gate-to-Source Voltage



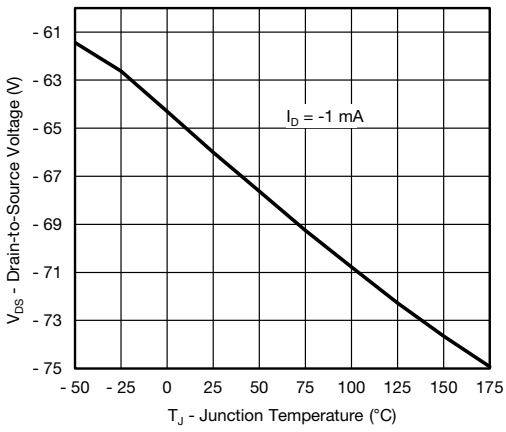
On-Resistance vs. Junction Temperature



Threshold Voltage

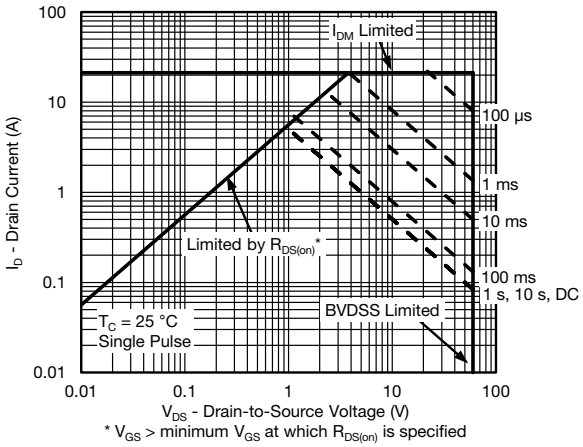


Source-Drain Diode Forward Voltage

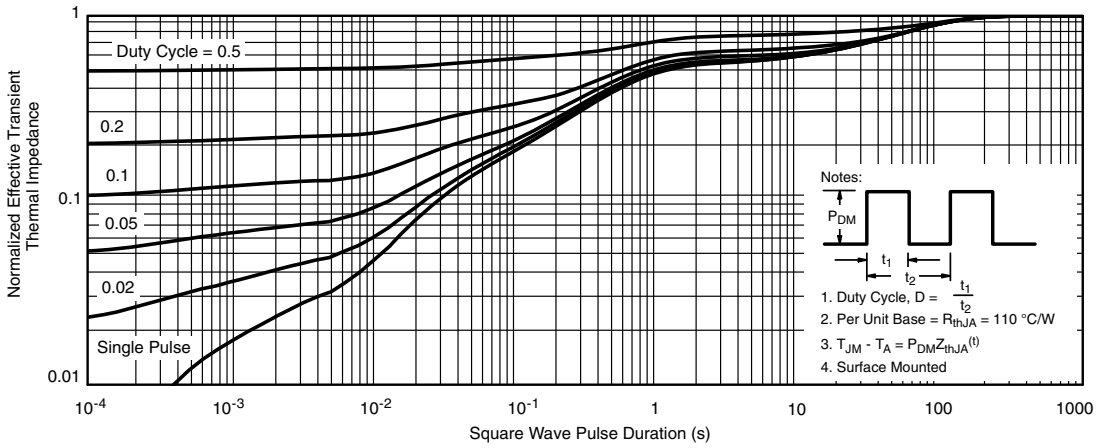


Drain-to-Source Voltage vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

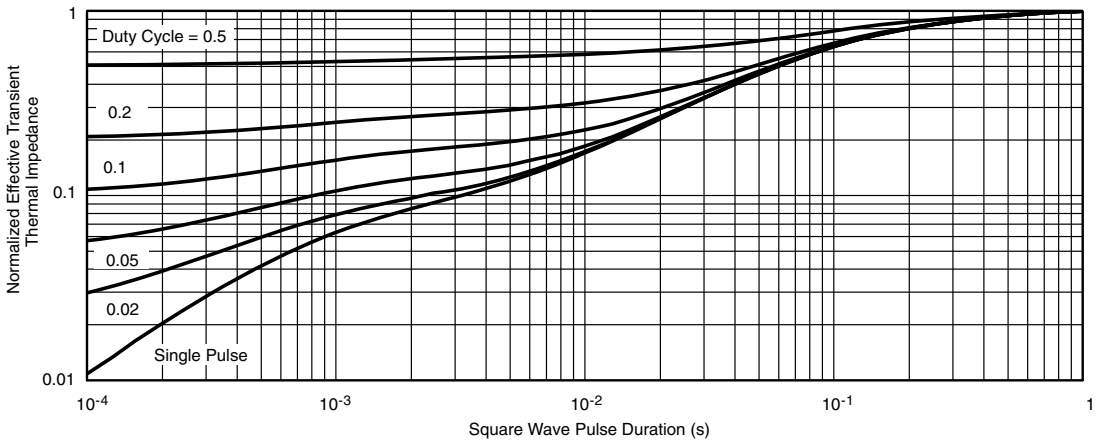


Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

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